SANCOM

SA-PAN027037-P52

2.7-3.7 GHz High Power GaN-HEMT

Features

Frequency Range: 2.7-3.7 GHz

P_{sat}: ≥ 52 dBm

Power Gain: ≥ 12 dB

Efficiency: ≥ 50%

Z_{in}/ Z_{out} = 50 Ω

Description

Sancom Electric's GaN-HEMT SA-PAN027037-P52 offers high power, high efficiency, ease of matching and greater consistency for high power applications with 32V operation. The SA-PAN027037-P52 typically provides 52 dBm of saturated output power and 12 dB of large-signal gain and can be widely used in various RF/microwave systems.

ABSOLUTE MAXIMUM RATINGS

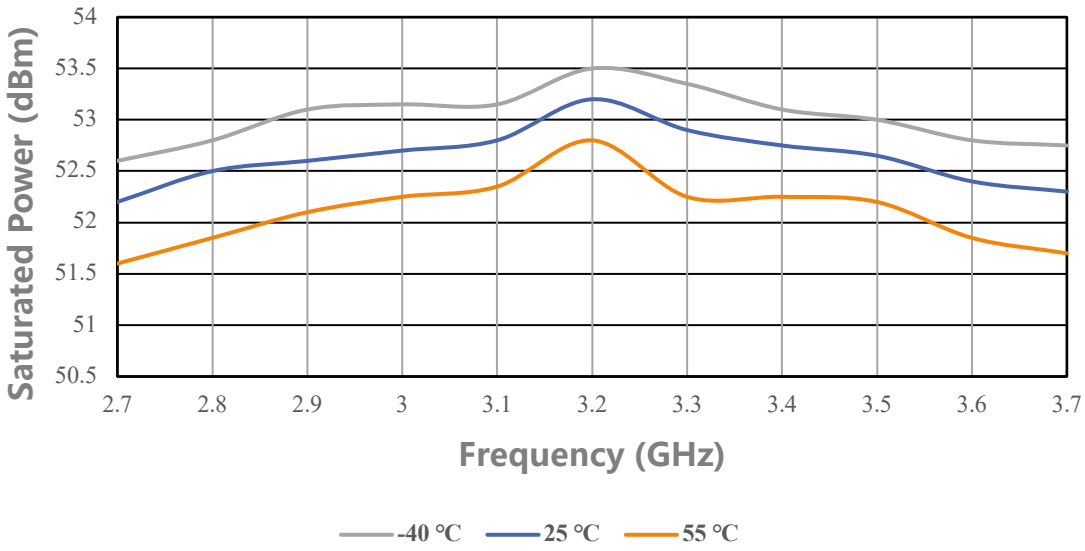
Parameter	Symbol	Condition	Rating	Unit
Drain-Source Voltage	V_{DS}	TC=25℃	40	V
Gate-Source Voltage	V_{GS}	TC=25℃	-5	V
Storage Temperature	T_{stg}	TC=25℃	-65 to 150	℃
Channel Temperature	T_{ch}	TC=25℃	150	℃

ELECTRICAL SPECIFICATIONS

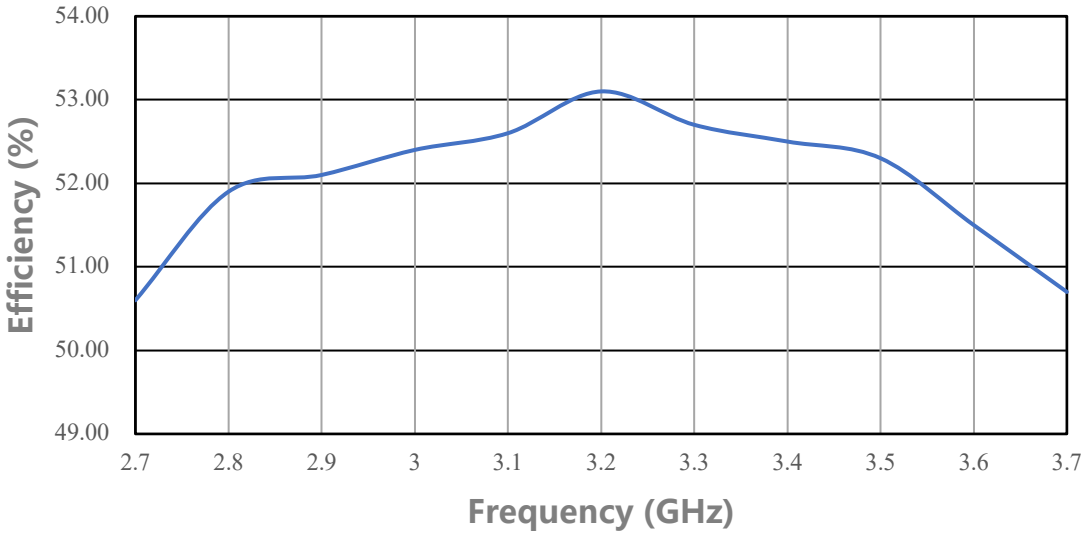
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Drain-Source Current	I_{DS}	V_{DS}: 32 V	-	9.9	-	A
Saturated Power	P_{sat}	Pulse	52	-	-	dBm
Power Gain	G_p	T=1ms, Duty=10%	12	-	-	dB
Efficiency	η	P_{in}: 40 dBm	50	-	-	%
Flatness	ΔG	Freq: 2.7 ~ 3.7 GHz	-0.8	-	0.8	dB

Performance Plots

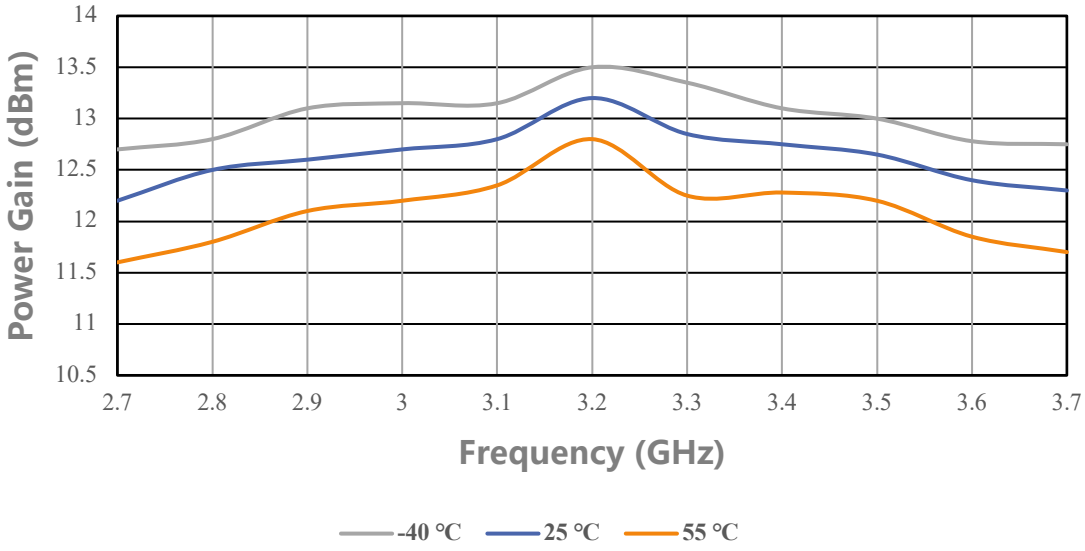
Saturated Power VS Frequency



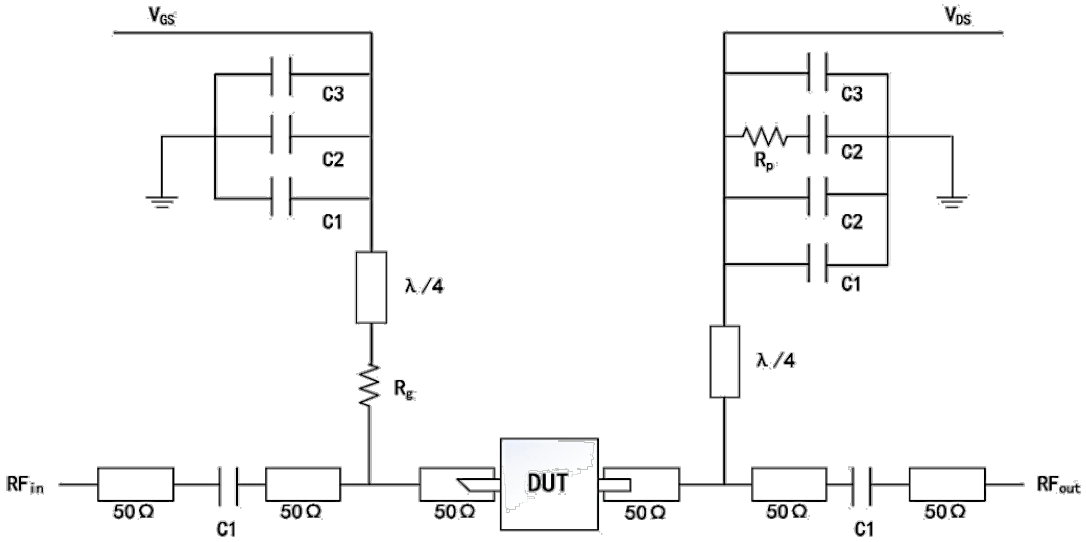
Efficiency VS Frequency



Power Gain VS Frequency



Simplified Block Diagram

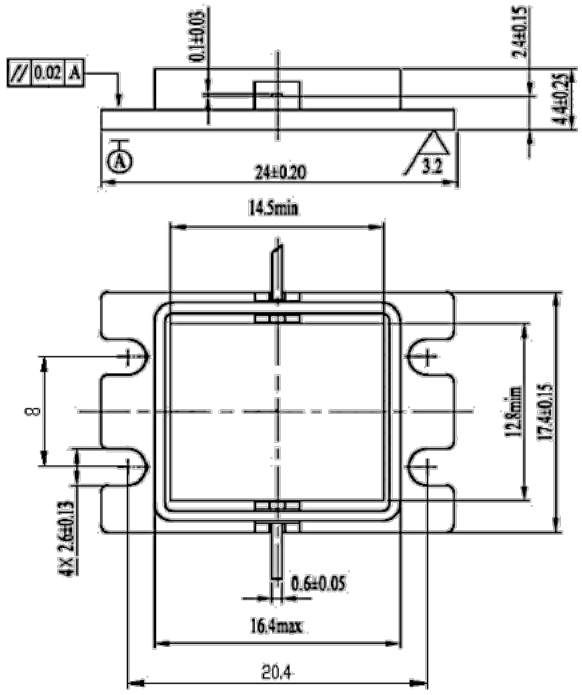


DUT information	
C1: 8 pF	Rp: 51 Ω
C2: 1000 pF	Rg: 15 Ω
C3: 100 μF	

ESD Protection

ESD	Class Ⅲ	2000 V

Outline Drawing



Unit: mm

Attention

- Please keep away from moisture during transportation and storage
- Pay attention to ESD prevention during chip use and assembly. Wear a grounding ESD bracelet.
- When adding electricity, add gate electricity first and then add leakage electricity